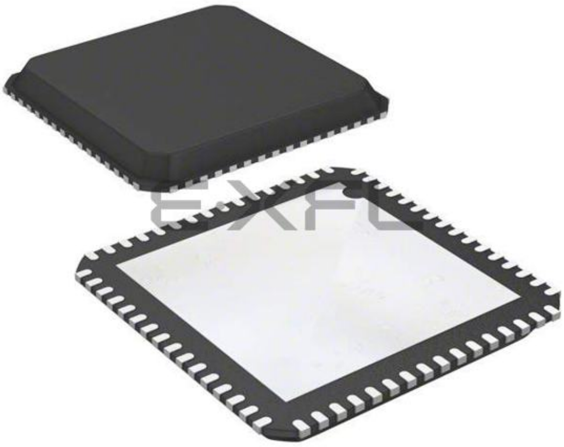

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg330f256-qfn64t

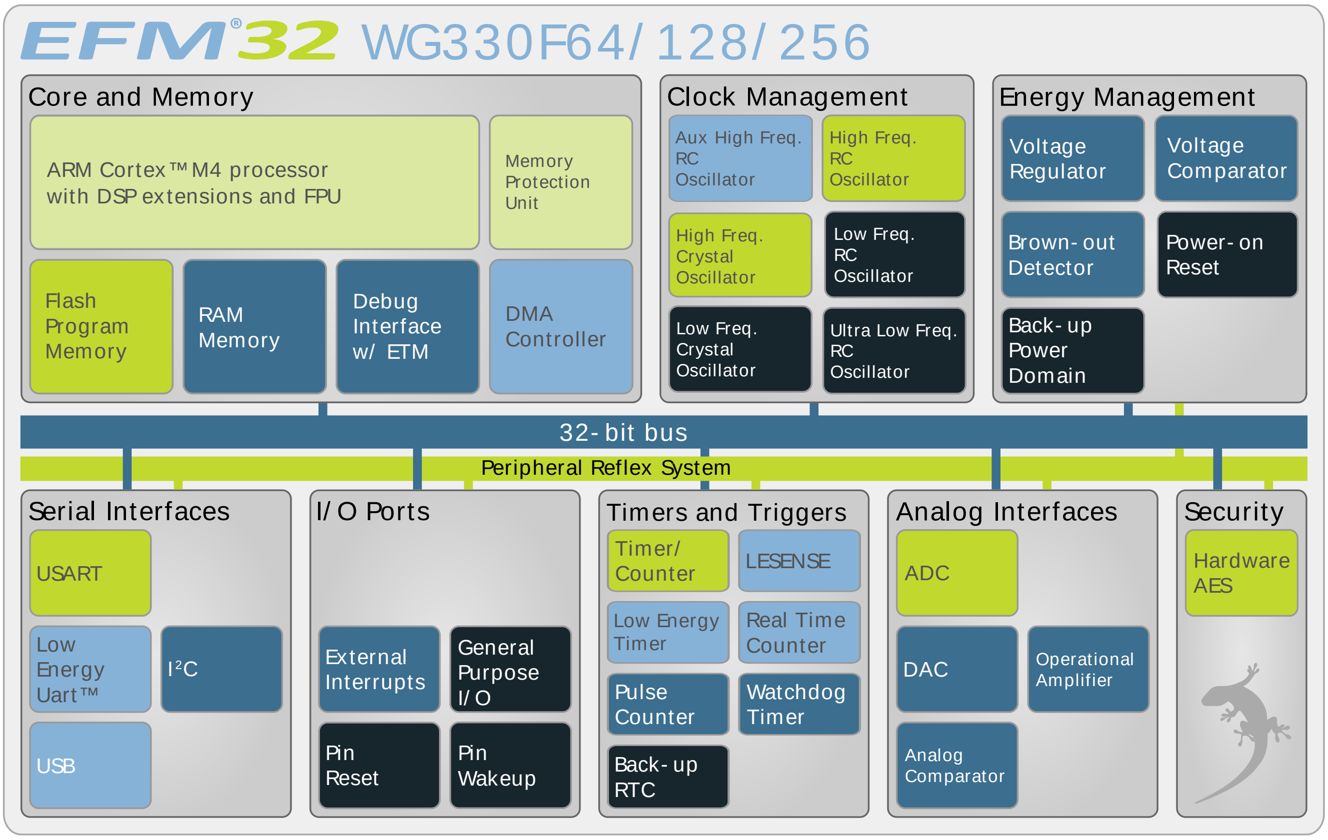
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M4, with DSP instruction support and floating-point unit, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32WG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32WG330 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32WG Reference Manual*.

A block diagram of the EFM32WG330 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M4 Core

The ARM Cortex-M4 includes a 32-bit RISC processor, with DSP instruction support and floating-point unit, which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M4 is described in detail in *ARM Cortex-M4 Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.26 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG330 to keep track of time and retain data, even if the main power source should drain out.

2.1.27 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.28 General Purpose Input/Output (GPIO)

In the EFM32WG330, there are 52 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32WG330 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
USB	Full configuration	USB_VBUS, USB_VBUSEN, USB_VREGI, USB_VREGO, USB_DM, USB_DMPU, USB_DP, USB_ID

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1]Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

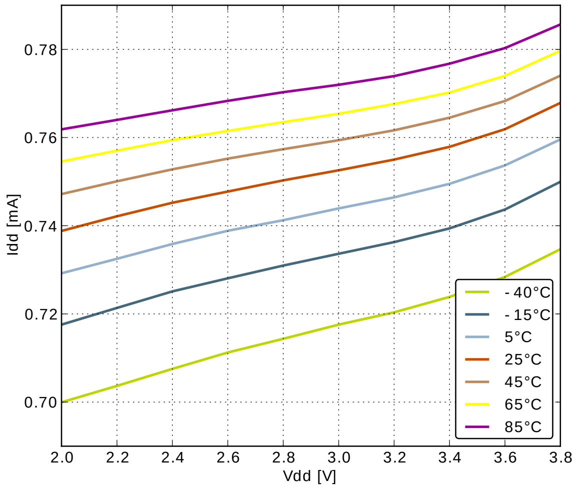
3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Figure 3.5. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11MHz



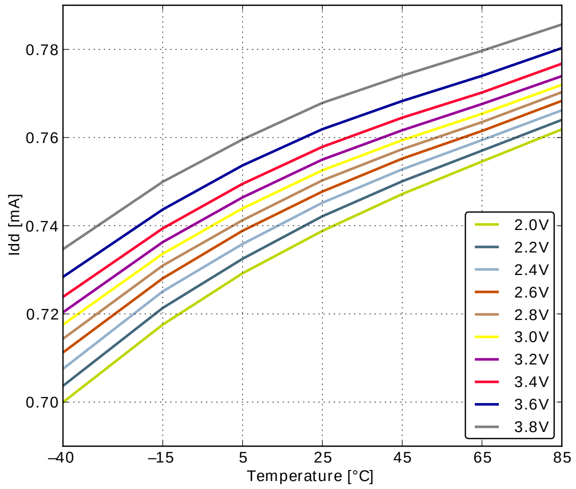
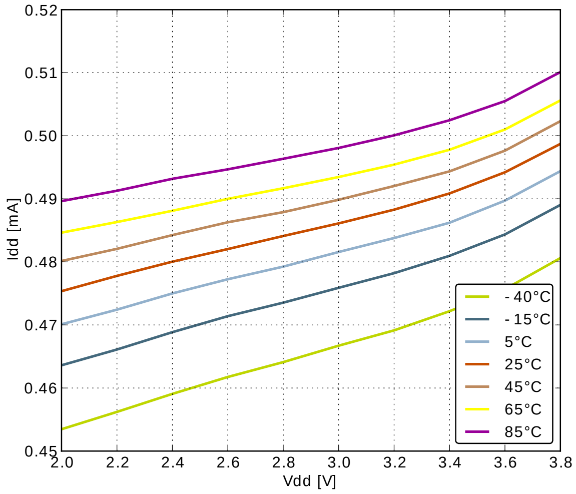


Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6MHz



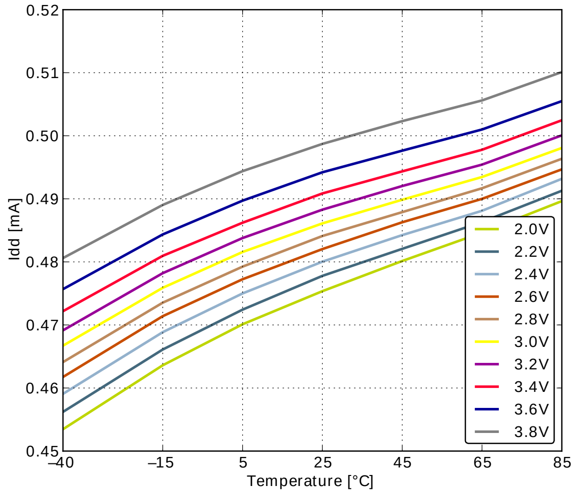
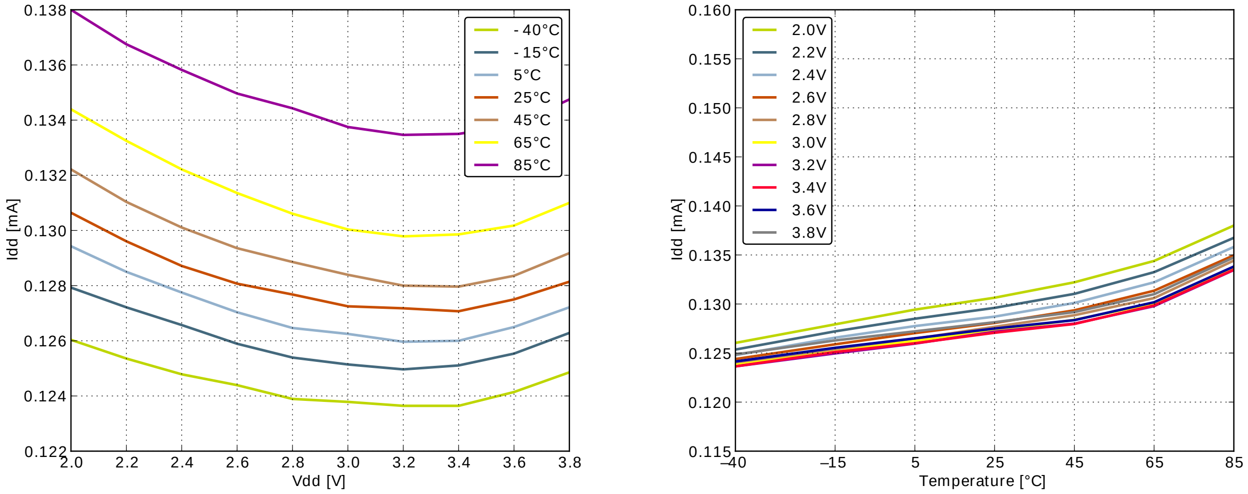
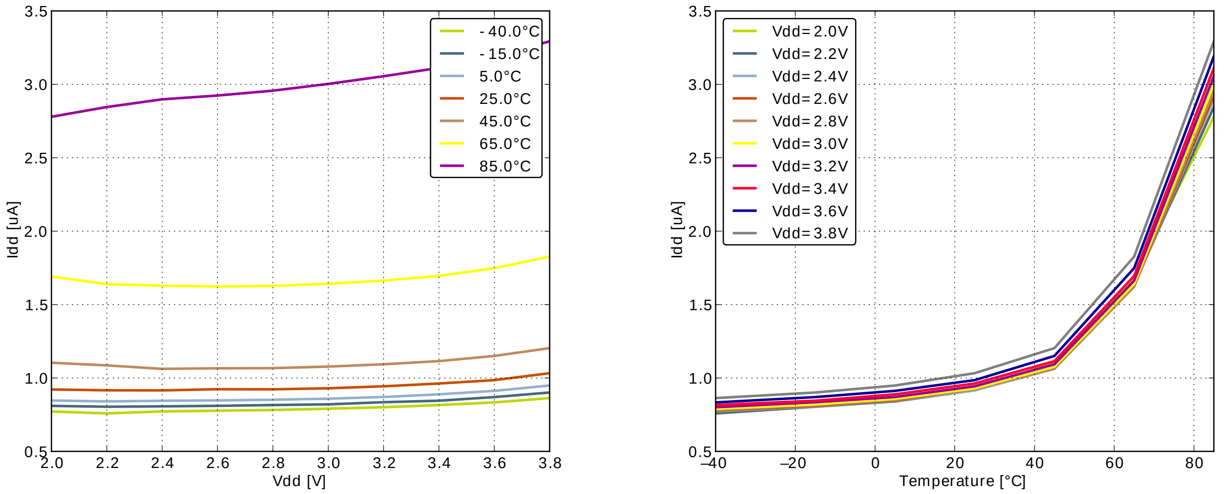


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 1.2MHz



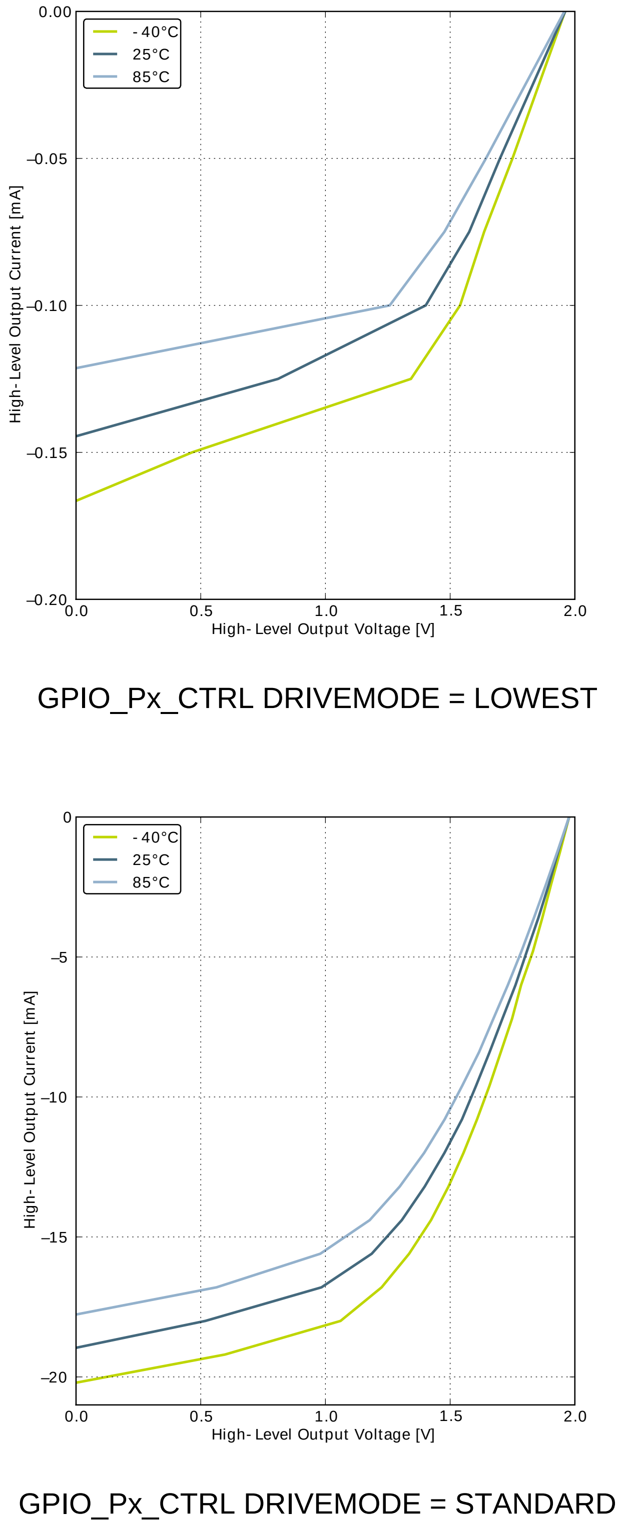
3.4.2 EM2 Current Consumption

Figure 3.8. EM2 current consumption. RTC[1] prescaled to 1kHz, 32.768 kHz LFRCO.



[1]Using backup RTC.

Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



3.9 Oscillators

3.9.1 LFXO

Table 3.9. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1]See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.10. HFXO

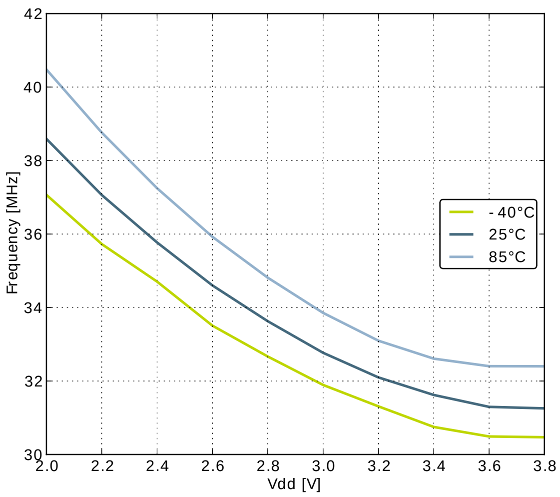
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs

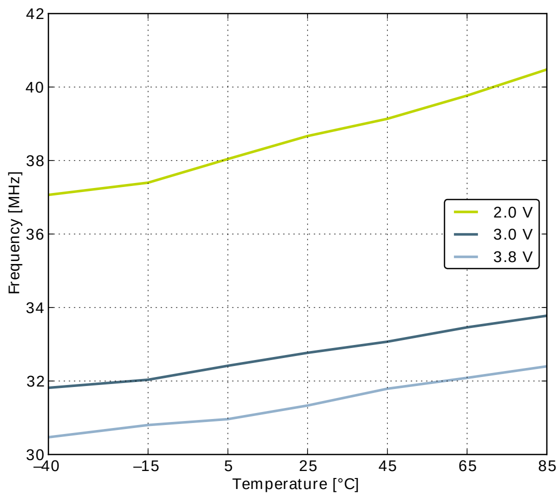
3.9.3 LFRCO

Table 3.11. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency , V_{DD}= 3.0 V, T_{AMB}=25°C		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		µs
I_{LFRCO}	Current consumption			300		nA
$TUNESTEP_{LFRCO}$	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.17. Calibrated LFRCO Frequency vs Temperature and Supply Voltage





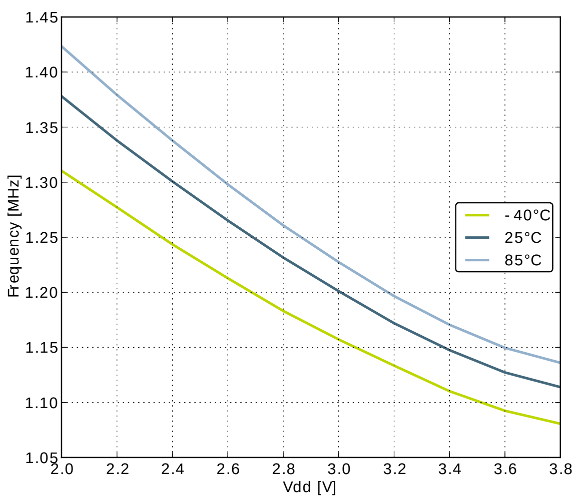
3.9.4 HFRCO

Table 3.12. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48	6.60	6.72	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{HFRCO\_settling}$	Settling time after start-up	f_{HFRCO} = 14 MHz		0.6		Cycles
I_{HFRCO}	Current consumption	f_{HFRCO} = 28 MHz		165	215	µA
		f_{HFRCO} = 21 MHz		134	175	µA
		f_{HFRCO} = 14 MHz		106	140	µA
		f_{HFRCO} = 11 MHz		94	125	µA
		f_{HFRCO} = 6.6 MHz		77	105	µA
		f_{HFRCO} = 1.2 MHz		25	40	µA
DC_{HFRCO}	Duty cycle	f_{HFRCO} = 14 MHz	48.5	50	51	%
$TUNESTEP_{HFRCO}$	Frequency step for LSB change in TUNING value			0.3[1]		%

[1]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.18. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature



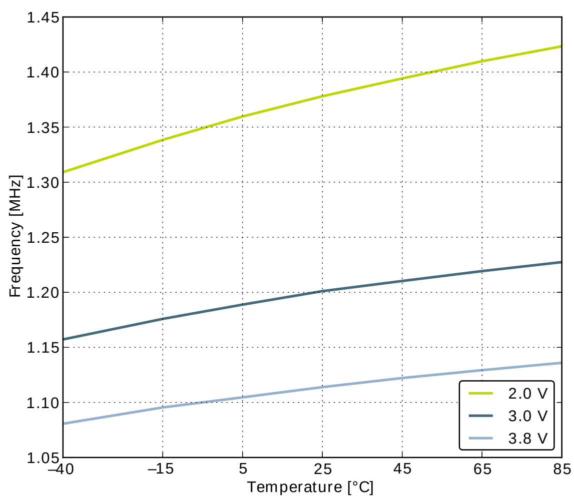


Figure 3.19. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

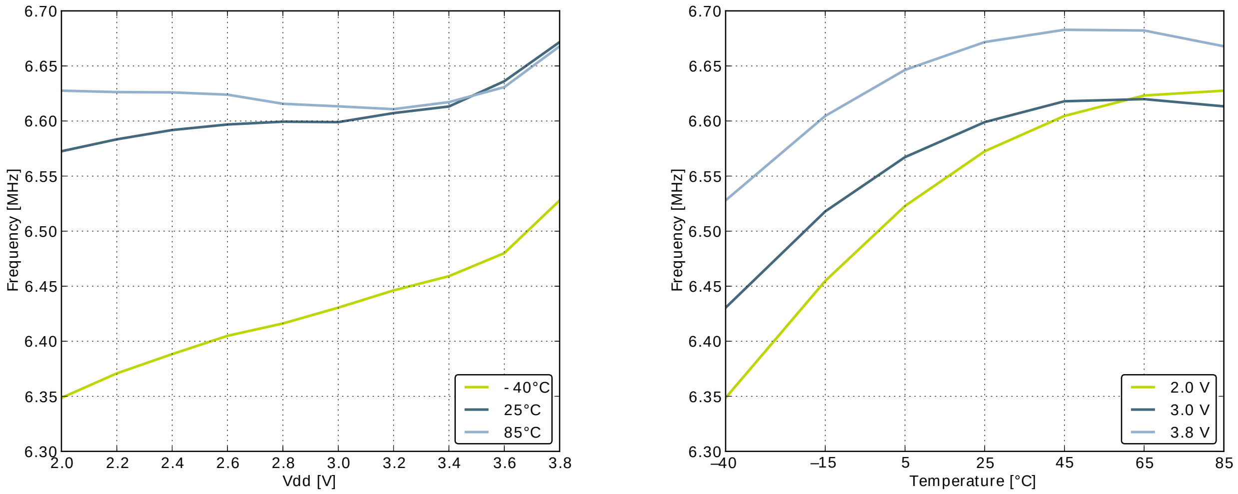


Figure 3.20. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

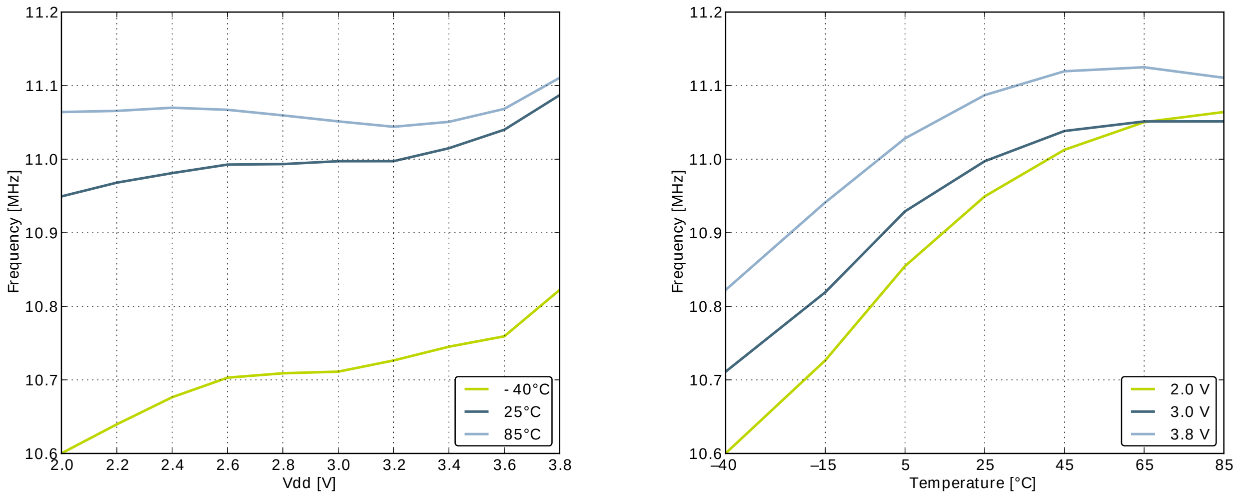


Figure 3.21. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

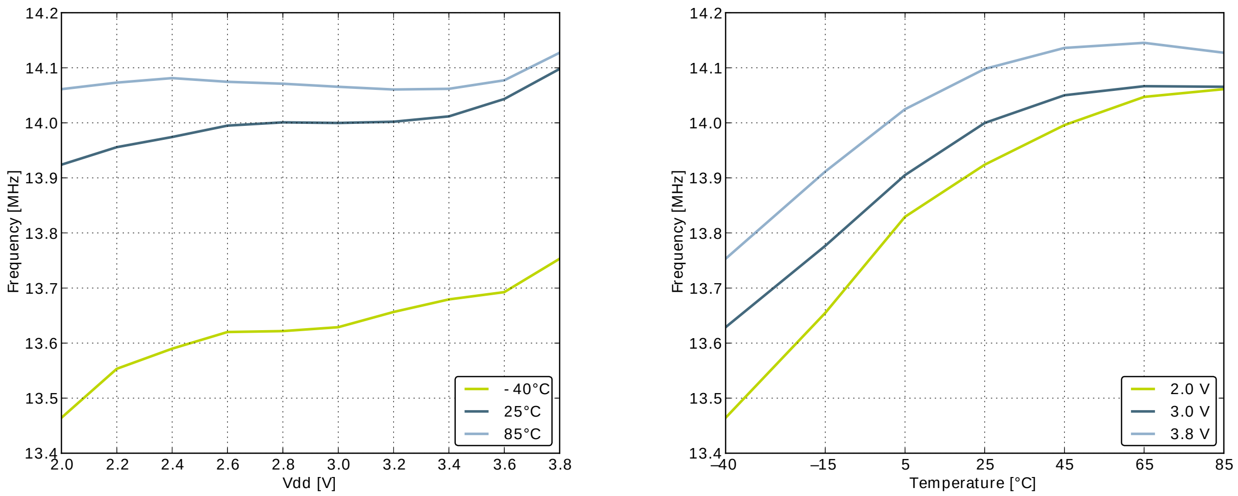
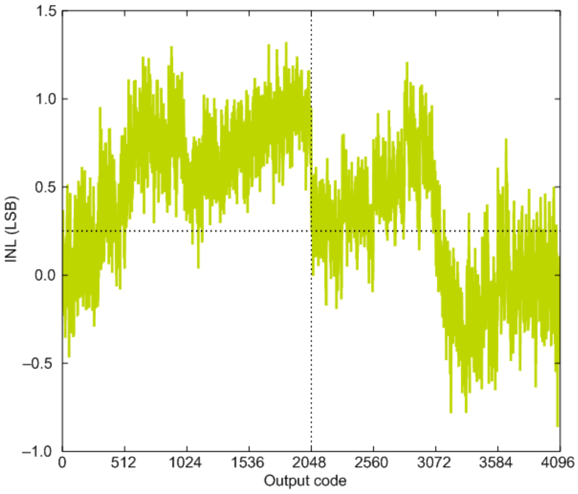
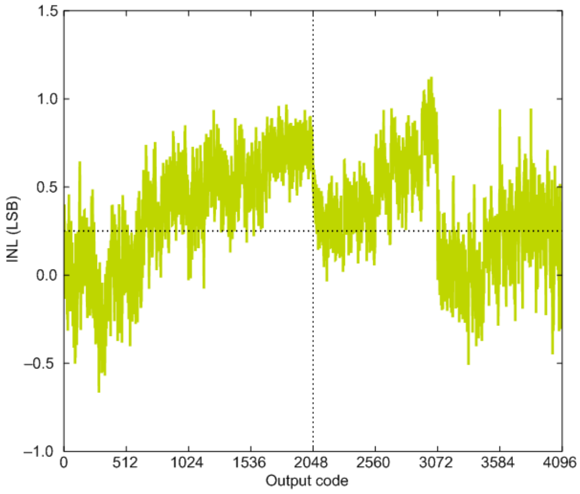


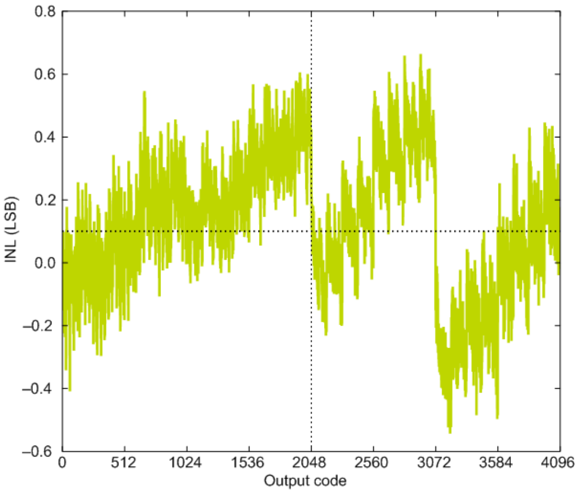
Figure 3.27. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



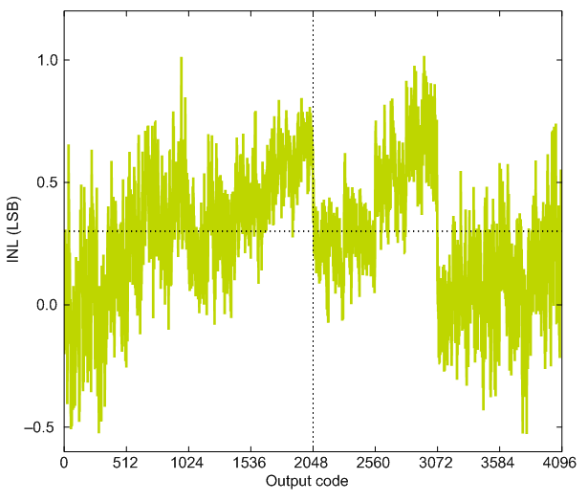
1.25V Reference



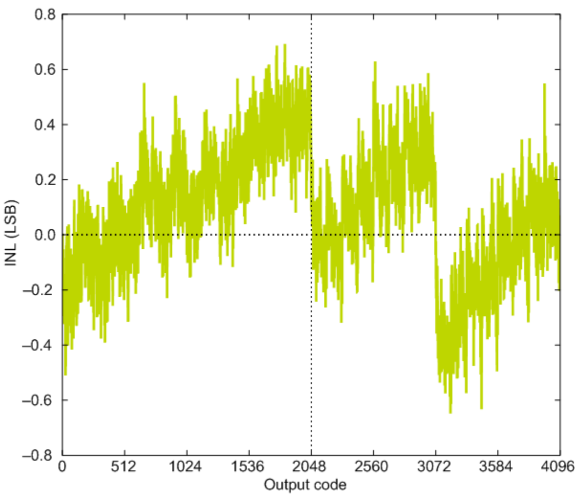
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
$SNDR_{DAC}$	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
$SFDR_{DAC}$	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
$V_{DACOFFSET}$	Offset voltage	After calibration, single ended		2	9	mV
		After calibration, differential		2		mV
DNL_{DAC}	Differential non-linearity			±1		LSB
INL_{DAC}	Integral non-linearity			±5		LSB
MC_{DAC}	No missing codes			12		bits

[1]Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	µA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	µA

Table 3.21. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and a START condition	1.3			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.22. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and a START condition	0.5			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32WG Reference Manual.

3.16 USART SPI

Figure 3.38. SPI Master Timing

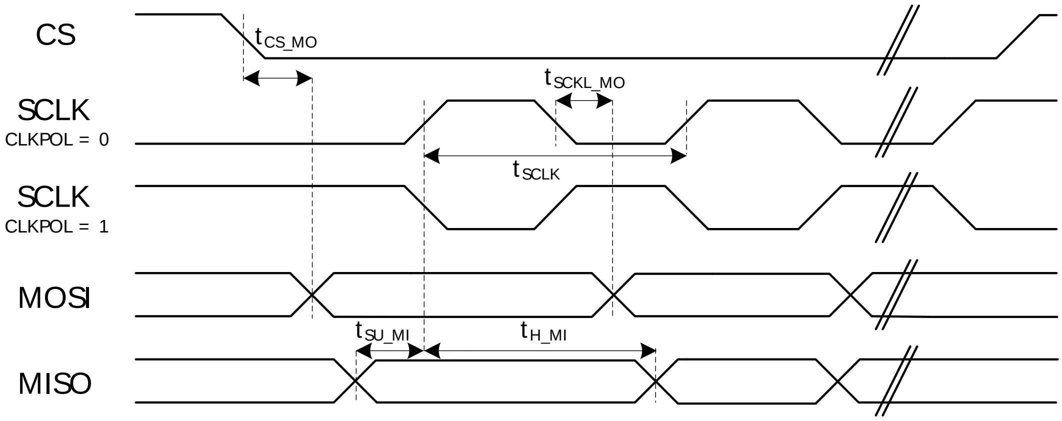


Table 3.23. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1,2]	SCLK period		2 * $t_{HFPERCLK}$			ns
t_{CS_MO} [1,2]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [1,2]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [1,2]	MISO setup time	IOVDD = 3.0 V	36.00			ns
t_{H_MI} [1,2]	MISO hold time		-6.00			ns

[1] Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.24. SPI Master Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1,2]	SCLK period		2 * $t_{HFPERCLK}$			ns
t_{CS_MO} [12]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [12]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [12]	MISO setup time	IOVDD = 3.0 V	-32.00			ns
t_{H_MI} [12]	MISO hold time		63.00			ns

[1] Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.39. SPI Slave Timing

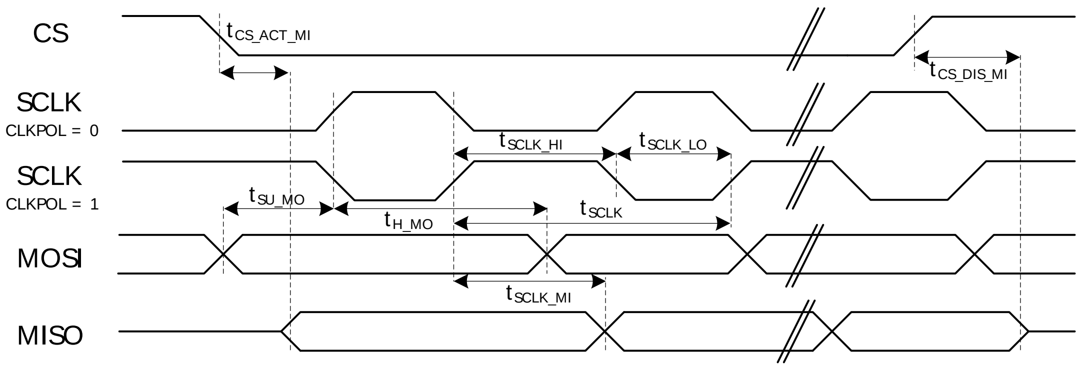


Table 3.25. SPI Slave Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_sl} [1 2]	SCKL period	6 * $t_{HFPERCLK}$			ns
t_{SCLK_hi} [1 2]	SCLK high period	3 * $t_{HFPERCLK}$			ns
t_{SCLK_lo} [1 2]	SCLK low period	3 * $t_{HFPERCLK}$			ns
$t_{CS\_ACT\_MI}$ [1 2]	CS active to MISO	5.00		35.00	ns
$t_{CS\_DIS\_MI}$ [1 2]	CS disable to MISO	5.00		35.00	ns
t_{SU_MO} [1 2]	MOSI setup time	5.00			ns
t_{H_MO} [1 2]	MOSI hold time	2 + 2 * $t_{HFPERCLK}$			ns
t_{SCLK_MI} [1 2]	SCLK to MISO	7 + $t_{HFPERCLK}$		42 + 2 * $t_{HFPERCLK}$	ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.26. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_sl} [12]	SCKL period	6 * $t_{HFPERCLK}$			ns
t_{SCLK_hi} [12]	SCLK high period	3 * $t_{HFPERCLK}$			ns
t_{SCLK_lo} [12]	SCLK low period	3 * $t_{HFPERCLK}$			ns
$t_{CS\_ACT\_MI}$ [12]	CS active to MISO	5.00		35.00	ns
$t_{CS\_DIS\_MI}$ [12]	CS disable to MISO	5.00		35.00	ns
t_{SU_MO} [12]	MOSI setup time	5.00			ns
t_{H_MO} [12]	MOSI hold time	2 + 2 * $t_{HFPERCLK}$			ns

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32WG330.

4.1 Pinout

The *EFM32WG330* pinout is shown in Figure 4.1 (p. 54) and Table 4.1 (p. 54). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32WG330 Pinout (top view, not to scale)

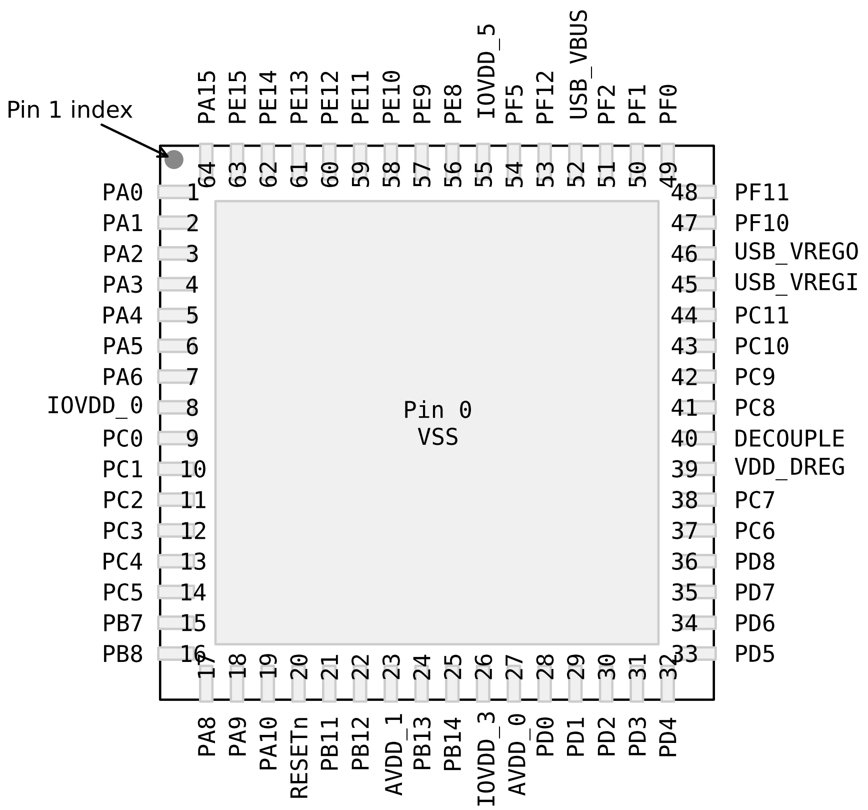


Table 4.1. Device Pinout

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground			
1	PA0		TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0
2	PA1		TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
		OPAMP_OUT2 #1			
29	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT	TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
30	PD2	ADC0_CH2	TIM0_CC1 #3	USB_DMPU #0 US1_CLK #1	DBG_SWO #3
31	PD3	ADC0_CH3 OPAMP_N2	TIM0_CC2 #3	US1_CS #1	ETM_TD1 #0/2
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	ETM_TD2 #0/2
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	ETM_TD3 #0/2
34	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2 ETM_TD0 #0
35	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
36	PD8	BU_VIN			CMU_CLK1 #1
37	PC6	ACMP0_CH6		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2
38	PC7	ACMP0_CH7		LEU1_RX #0 I2C0_SCL #2	LES_CH7 #0 ETM_TD0 #2
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.			
41	PC8	ACMP1_CH0	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
42	PC9	ACMP1_CH1	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
43	PC10	ACMP1_CH2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
44	PC11	ACMP1_CH3		US0_TX #2	LES_CH11 #0
45	USB_VREGI	USB Input to internal 3.3 V regulator.			
46	USB_VREGO	USB Decoupling for internal 3.3 V USB regulator and regulator output.			
47	PF10			USB_DM	
48	PF11			USB_DP	
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1/2/3
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
51	PF2		TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	USB_VBUS	USB 5.0 V VBUS input.			
53	PF12			USB_ID	
54	PF5		TIM0_CDTI2 #2/5	USB_VBUSEN #0	PRS_CH2 #1
55	IOVDD_5	Digital IO power supply 5.			
56	PE8		PCNT2_S0IN #1		PRS_CH3 #1

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
GPIO_EM4WU3	PF1							Pin can be used to wake the system up from EM4
GPIO_EM4WU4	PF2							Pin can be used to wake the system up from EM4
GPIO_EM4WU5	PE13							Pin can be used to wake the system up from EM4
HFXTAL_N	PB14							High Frequency Crystal negative pin. Also used as external optional clock input pin.
HFXTAL_P	PB13							High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7	PC7		PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6	PC6		PC0	PF0	PE12	I2C0 Serial Data input / output.
I2C1_SCL	PC5	PB12						I2C1 Serial Clock Line input / output.
I2C1_SDA	PC4	PB11						I2C1 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX2	PA3							LESENSE alternate exite output 2.
LES_ALTEX3	PA4							LESENSE alternate exite output 3.
LES_ALTEX4	PA5							LESENSE alternate exite output 4.
LES_ALTEX5	PE11							LESENSE alternate exite output 5.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH2	PC2							LESENSE channel 2.
LES_CH3	PC3							LESENSE channel 3.
LES_CH4	PC4							LESENSE channel 4.
LES_CH5	PC5							LESENSE channel 5.
LES_CH6	PC6							LESENSE channel 6.
LES_CH7	PC7							LESENSE channel 7.
LES_CH8	PC8							LESENSE channel 8.
LES_CH9	PC9							LESENSE channel 9.
LES_CH10	PC10							LESENSE channel 10.
LES_CH11	PC11							LESENSE channel 11.
LETIM0_OUT0	PD6	PB11	PF0	PC4				Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7	PB12	PF1	PC5				Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14	PE15	PF1	PA0			LEUART0 Receive input.
LEU0_TX	PD4	PB13	PE14	PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LEU1_RX	PC7	PA6						LEUART1 Receive input.
LEU1_TX	PC6	PA5						LEUART1 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7							Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN			PC0	PD6				Pulse Counter PCNT0 input number 0.
PCNT0_S1IN			PC1	PD7				Pulse Counter PCNT0 input number 1.

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
								USART2 Synchronous mode Master Input / Slave Output (MISO).
US2_TX	PC2							USART2 Asynchronous Transmit.Also used as receive input in half duplex communication. USART2 Synchronous mode Master Output / Slave Input (MOSI).
USB_DM	PF10							USB D- pin.
USB_DMPU	PD2							USB D- Pullup control.
USB_DP	PF11							USB D+ pin.
USB_ID	PF12							USB ID pin. Used in OTG mode.
USB_VBUS	USB_VBUS							USB 5 V VBUS input.
USB_VBUSEN	PF5							USB 5 V VBUS enable.
USB_VREGI	USB_VREGI							USB Input to internal 3.3 V regulator
USB_VREGO	USB_VREGO							USB Decoupling for internal 3.3 V USB regulator and regulator output

4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32WG330* is shown in Table 4.3 (p. 61). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port in indicated by a number from 15 down to 0.

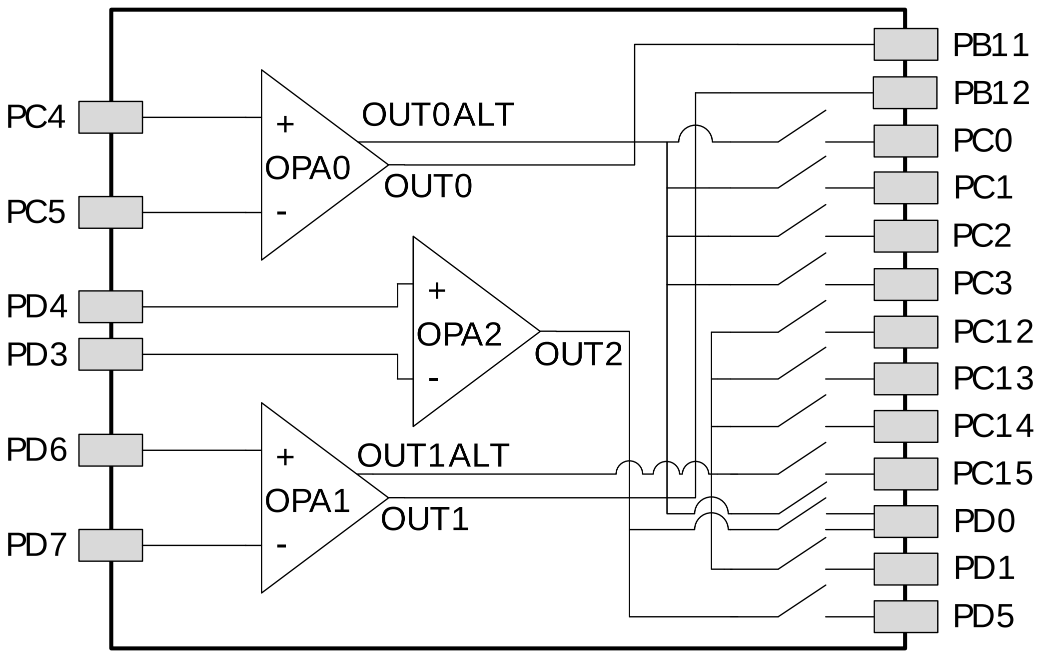
Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	-	-	-	-	PA10	PA9	PA8	-	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	-	-	-	-	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	-	-	-	-	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	-	-	-	-	-	-	-	-
Port F	-	-	-	PF12	PF11	PF10	-	-	-	-	PF5	-	-	PF2	PF1	PF0

4.4 Opamp Pinout Overview

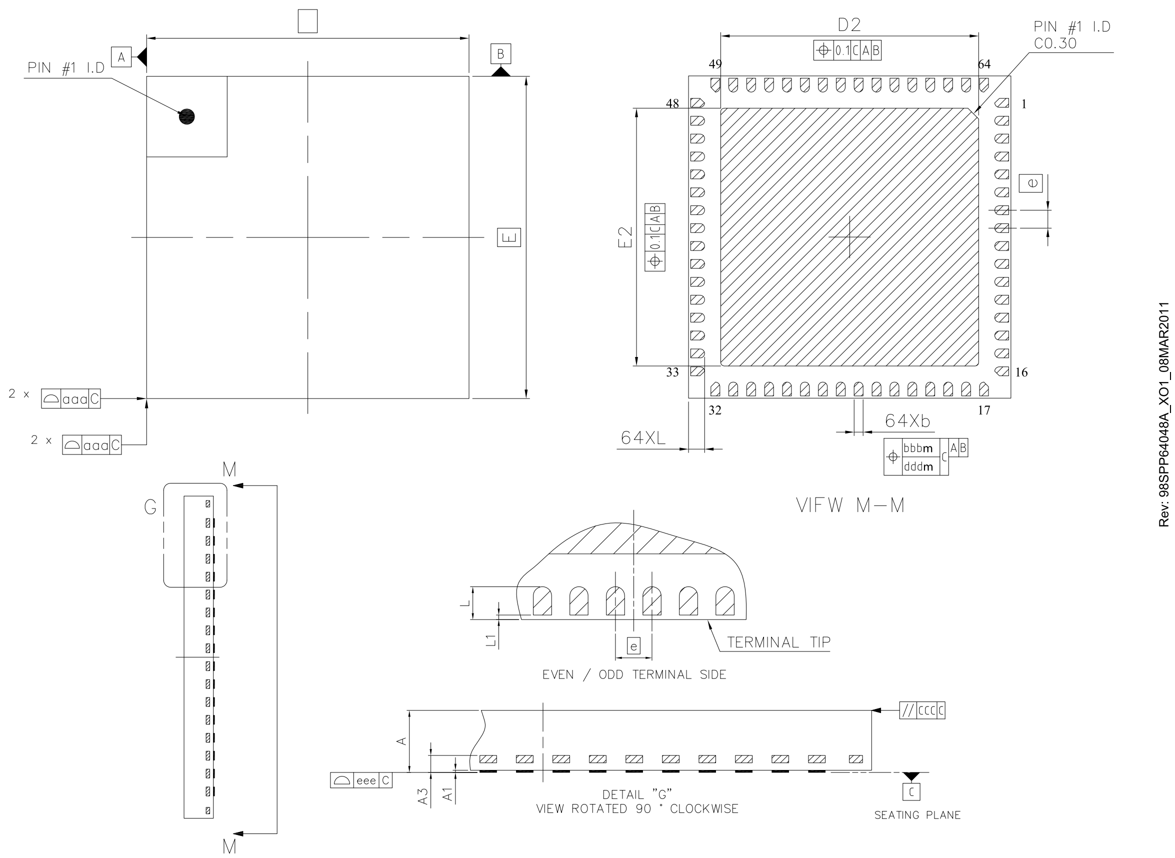
The specific opamp terminals available in *EFM32WG330* is shown in Figure 4.2 (p. 62) .

Figure 4.2. Opamp Pinout



4.5 QFN64 Package

Figure 4.3. QFN64



Note:

1. Dimensioning & tolerancing confirm to ASME Y14.5M-1994.
2. All dimensions are in millimeters. Angles are in degrees.